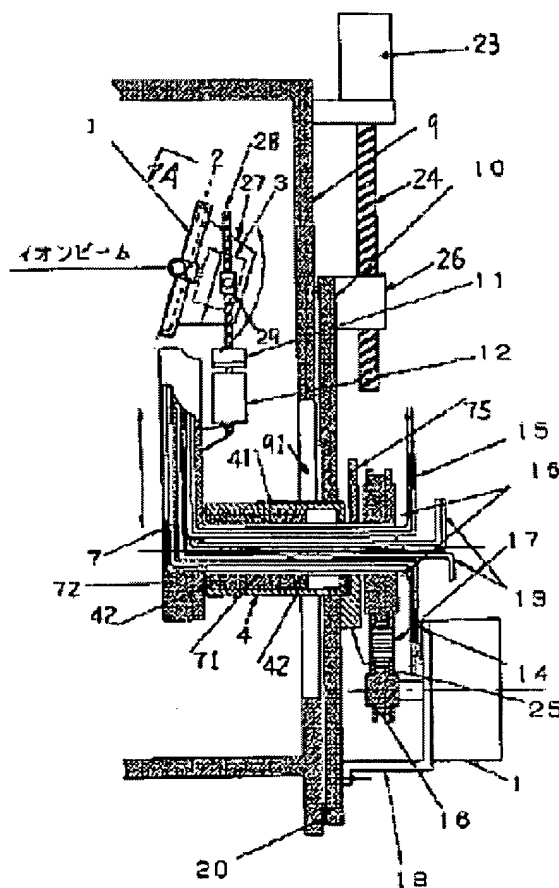


ION IMPLANTER

Patent number: JP11007915
Publication date: 1999-01-12
Inventor: HIDAKA YOSHITOMO; OKADA KEIJI
Applicant: SUMITOMO EATON NOBA KK
Classification:
- international: H01J37/317; H01L21/265
- european:
Application number: JP19970158617 19970616
Priority number(s):

Abstract of JP11007915

PROBLEM TO BE SOLVED: To provide an ion implanter of a sheet capable of uniformly implanting ions to a semiconductor wafer with an emitting direction of an ion beam fixed.
SOLUTION: An emitting direction of an ion beam is fixed. Ions are implanted to a semiconductor wafer 1 while the semiconductor wafer 1 is mechanically moved laterally and vertically. For this purpose, an oscillating mechanism is provided for reciprocally and laterally moving a wafer platen 2, which holds the semiconductor wafer 1 therein, at a constant speed inside a vacuum container 9, and a vertically driving mechanism is provided for vertically moving the wafer platen 2 at another constant speed.



Data supplied from the esp@cenet database - Patent Abstracts of Japan

BEST AVAILABLE COPY